CURRICULUM VITAE
Dr. Kelin J. Kuhn

CONTACT INFORMATION:

Kelin J. Kuhn
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EDUCATION:

Ph.D., Electrical Engineering, Stanford University, Stanford, CA. June 1985
M.S., Electrical Engineering, Stanford University, Stanford, CA. June 1985
B.S., Electrical Engineering, University of Washington, Seattle, WA. March 1980
(magna cum laude)

PRESENT ROLE:

Confluence Technology Services, Winthrop, WA (kjkuhn@confluence-tech.com); present role

Dr. Kuhn's business (Confluence Technology Services) supports a variety of engineering services in electronics and photonics, with emphasis on CMOS and beyond-CMOS technologies.

Cornell University, Ithaca, NY; Materials Science and Engineering (kjk236@cornell.edu) 2014 to date

Position: Adjunct Professor
Key Collaborator: Darrell Schlom

Prof. Kuhn's role is collaborating with a diverse group of faculty (both at Cornell and elsewhere) for establishment of long-term research programs in the area of valleytronics, inverse-design, quantum materials, post-CMOS technology, and spintronics.

CLIENTS / SIGNIFICANT INTERACTIONS POST-2014:

Wolf Greenfield: Initiated 2020 and on-going. Technical evaluation and consulting in the matter of *Godo Kaisha IP Bridge 1 v. Micron Technology et al.*.

Hueston Henningan: Initiated 2020 and on-going. Technical evaluation and consulting in the matter of *Acorn Semi, LLC v. Samsung Electronics et al.*

Susman Godfrey: Initiated 2020 and on-going. Technical evaluation and consulting with regards to *Arigna Technology Limited* on matters related to CMOS transistor design.

Quinn Emanuel Urquhart & Sullivan: Initiated 2020 and on-going. Technical evaluation and consulting in the matter of *Godo Kaisha IP Bridge 1 v. Micron Technology et al.*

Skadden Arps: Initiated 2020 and on-going. Technical consulting for the *Audit Committee of the Intel Board of Directors* on matters related to Technology Development.

Womble Bond Dickinson: Completed 2020. Technical consulting for KIPB LLC (formerly KAIST IP US LLC) on an ex parte reexamination ("EPR") proceeding in the United States Patent and Trademark Office with regards to patent 6,885,055.

PARADIM: Initiated 2016 and on-going. PARADIM's mission is to create new interface materials with unprecedented properties for the next generation of electronic devices. Dr. Kuhn is a member of the External Advisory Committee. In this role, Dr. Kuhn provides technical and management support with regards to PARADIM operations.

Womble Bond Dickinson: Completed, 2020. Technical evaluation and consulting in the matter of *KIPB LLC v. Samsung Electronics et al*. Dr. Kuhn supported this litigation for the plantiff as an expert witness, including completion of the Infringement and Rebuttal Reports, as well as completing a deposition conducted on the contents of the Infringement and Rebuttal Reports. This case was settled out of court in September 2020.

Lathrop Gage: Completed, 2018-2020. Technical evaluation and consulting for KIPB LLC (formerly KAIST IP US LLC) on Korean Patent 10-0458288 (Korean counterpart to US 6,885,055).

Ropes & Gray: Completed, 2018. Technical evaluation and consulting in the matter of *Godo Kaisha IP Bridge 1 v. Qualcomm Inc. et al.*

GlaserWeil: Completed, 2016-2018. Technical evaluation and consulting in the matter of *KAIST IP US LLC v. Samsung Electronics Co., Ltd., Case No. 2:16-cv-01314.* Dr. Kuhn supported this litigation for the plantiff as an expert witness. This included IPR proceedings (a total of 6 IPRs were presented to the PTO in this case). This also included completion and submission of the Claim Construction Declaration, the Infringement Report, and the Rebuttal Report, as well as depositions conducted on the contents of these Reports. This case went to trial June 11-15, where Dr. Kuhn presented both Direct testimony on infringement (6/12/18) and Rebuttal (6/14/18) testimony on validity.

yoR Labs Inc.: Completed. 2015-2017. yoR Labs is a medical instrumentation start-up, focusing on non-invasive medical imaging instrumentation. Dr. Kuhn served first as a member of the External Advisory Committee and later as a member of the Board of Directors. In this role, Dr. Kuhn provided technical and management support with regards to yoR labs operations.

Oregon State University, Department of Electrical Engineering and Computer Science: Completed. 2015 to 2018: Professor-courtesy. Prof. Kuhn's role was establishment of long-term research programs in the area advanced CMOS technology and post-CMOS technology.

FORMER ROLES (2014 and PRIOR)

Intel, Portland, OR, (advanced development / research) 2008-2014 (retired in 2014)
Grade level: 12 (Fellow)
Manager: Mike Mayberry, VP

Dr. Kuhn's role was researching advanced device architectures for Intel processes in the 5-10 year time frame. While much of her work as an Intel Fellow remains proprietary, some of the public domain aspects are captured in her book *CMOS and Beyond: Logic Switches for Terascale Integrated Circuits* (Cambridge, 2015) and her paper "Considerations for Ultimate CMOS Scaling," (IEEE Trans. on Elec. Dev., Vol: 59 , No: 7, 2012 , pp. 1813 – 1828 which won the Paul Rappaport Award). She received an Intel IAA in 2008 for her work on the TriGate transistor.

Intel, Portland, OR, (45nm Device technology manager in pathfinding) 2004-2008
Grade level: 10/11 (Principal Engineer / Sr. Principal Engineer)
Manager: Mark Bohr, Senior Intel Fellow / Kaizad Mistry, VP

Dr. Kuhn's role was as device technology manager of the pathfinding team responsible for the high-k metal-gate transistor architecture for Intel's 45nm microprocessor processor technology. She received an Intel IAA in 2006 for her work on high-k metal-gate.

Intel, Portland, OR, (90nm communication process manager) 2001-2004+
Grade level: 9/10 (Sr. Engineer / Principal engineer)
Manager: Scott Thompson (was Intel Fellow at the time, now a professor at Univ. of Florida).

Dr. Kuhn's role in this time frame was Process Program Manager of the team responsible for Intel's 90nm communications process technology. Over a 4-year period, this team developed a derivative analog/RF technology (including a SiGe BJT) on top of Intel's premium 90nm microprocessor process.

Other Intel experience:

Intel, Portland, OR, (130nm front-end integration engineer) 1998-2001
Intel, Portland, OR, (0.35um front-end integration engineer) 1997-1998
Grade level: 7-9 (Sr. engineering grades)

During the 130nm generation, Dr. Kuhn was an integration engineer responsible for the isolation section of the flow. 130nm was the last of the "classic" CMOS generations, and her work in that generation was updating the isolation process. She had the satisfaction of watching the work she

did in the 130nm successfully scale through 90nm, 65nm, 45nm, and 32nm, with little change in the base process.

Dr. Kuhn joined Intel on the 0.35um generation as a sustaining integration engineer in F15. She was responsible for the silicide section of the flow. Additionally, she participated in the DIVD camera chip project (Intel's historical project to build CMOS camera chips).

Other relevant experience:

Univ. of Washington, Seattle, WA (Assoc. Prof., Ass't. Prof., Res. Ass't. Prof.), 1987-1997

Dr. Kuhn held faculty positions at the University of Washington (in Seattle) for roughly a decade in the order of Research Assistant Professor (Materials Science and Engineering), Assistant Professor (Electrical and Computer Engineering), and Associate Processor (Electrical and Computer Engineering). She left the University in 1997 as a tenured Associate Professor of Electrical and Computer Engineering. While at the Univ. of Washington, she achieved distinction in both research and teaching. Highlights include:

- University of Washington, Distinguished Teaching Award, 1995 (UW's highest level of achievement for a faculty member)
- NSF Presidential Young Investigator award, 1991-6 (The National Science foundation is the most prestigious funding agency for faculty and the NSF PYI award is the most prestigious national level award for junior faculty).
- Single-author on a textbook, Laser Engineering, Prentice-Hall, 1998, ISBN 0-02-366921-7 (this is a mezzanine text discussing the theory and practice of building conventional and diode laser systems).

BOOKS

Laser Engineering, (sole author) Prentice-Hall, 1998, ISBN 0-02-366921-7

CMOS and Beyond: Logic Switches for Terascale Integrated Circuits (Co-editor with Prof. Tsu-Jae King Liu, Cambridge Press, 2015, ISBN 978-1107043183).

BOOK CHAPTERS

Chapter 1, CMOS and Beyond CMOS: Scaling Challenges" (Book title: "High Mobility Materials for CMOS Applications", Woodhead Publishing Series in Electronic and Optical Materials, Elsevier, June 2018, ISBN 9780081020616)

AWARDS:

IEEE Frederik Philips Award (2016)
IEEE Paul Rappaport Award (2013)
IEEE Fellow (2011)

Intel Achievement Awards (Intel's highest technical award): IAA 2006 (for HiK-MG) and IAA 2008 (for key contributions to Intel's 22nm TriGate technology)
Intel Divisional Awards: Turbo operation (2009), RF Vccmin (2007), TCC (2005), SCD 1213.4 SCD/ICG (2004), LAD NW/Ophir A-1 (2003), SiGe BJT (2002), Hitachi etch (2002), 2um2SRAM (2001), Gamma Test chip (2000), Certification P854.6 (1999), F15 ISO 9000 (1998)
Academic Engineer of the Year Award, Puget Sound Engineering Council, 1996
University of Washington, Distinguished Teaching Award, 1995
College of Engineering, Outstanding Faculty Achievement Award, 1994
NSF Presidential Young Investigator award, 1991-6
NSF Research Initiation Award, 1989-91
IBM Graduate Fellowship, 1983-5
Hertz Graduate Fellowship, 1982-3
National Merit Scholar, 1976-80

JOURNAL PUBLICATIONS:

49. "First principles modeling of defects in the Al2O3 /In0.53Ga0.47 As system", G. Greene-Diniz, K. Kuhn, P. Hurley, and J. Greer, J. Appl. Phys., Vol. 121, No. 7, Jan. 2017.

48. "Doping top-down e-beam fabricated germanium nanowires using molecular monolayers," B. Long, G. Alessio Verni, J. O'Connell, M. Shayesteh, A. Gangnaik, Y.M. Georgiev, P. Carolan, D. O'Connell, K.J. Kuhn, S.B. Clendenning, R. Nagle, R. Duffy, and J.D. Holmes, Materials Science in Semiconductor Processing, Vol. 62, May 2017, pp. 196-200.

47. "Device Physics Modeling of Surfaces and Interfaces from an Induced Gap State Perspective," J. Wager and K. Kuhn, Critical Reviews in Solid State and Materials Science, Oct. 4, 2016.

46. "Adhesion Limits and Design Criteria for Nanorelays", Kevin L. Lin, Graham L. W. Cross, Peter Gleeson, Johann P. de Silva, Alejandro Levander, Jorge A. Muñoz, Chytra Pawashe, Alexis Potie, Patrick Theofanis, John J. Boland, and Dr. Kuhn J. Kuhn, IEEE Trans. on Elec. Dev., Vol. 63, No. 1, Jan. 2016, 465-470.

45. Distributive Quasi-Ballistic Drift Diffusion Model Including Effects of Stress and High Driving Field, Roza Kotlyar,, Rafael Rios, Cory E. Weber, Thomas D. Linton, Mark Armstrong and Dr. Kuhn Kuhn, IEEE Trans. on Elec. Dev., Vol. 62, No. 3, March 2015. Pp. 743-750.

44. Improved MOSFET characterization technique for single channel length, scaled transistors, Ferdousi, F., Rios, R., Kuhn K.J. Solid State Electronics, Vol. 104, pp. 44-6, Feb. 2015

43. Capacitance and Conductance for an MOS System in Inversion, with Oxide Capacitance and Minority Carrier Lifetime Extractions, Monaghan, S. O'Connor, E., Rios, R., Ferdousi, F., Floyd, L., Ryan, E., Cherhaoui, K., Povey, I.M., Kuhn, K.J., Hurley, P.K. IEEE Transactions on Electron Devices, Vol. 61, No. 12, pp. 4176-85, Dec. 2014.

42. First principle-based analysis of single-walled carbon nanotube and silicon nanowire Junctionless transistors, Ansari, L., Feldman, B., Faga, G., Martinez, L.C., Haverty, M.G., Kuhn, K.J., Shankar, S., Greer, J.C., IEEE Transactions on Nanotechnology, Vol. 12, No. 6, pp. 1075-81, Nov. 2013.

41. Scaling Limits of Electrostatic Nanorelays, Pawashe, C., Lin, K., Kuhn, K.J., IEEE Transactions on Electron Devices, Vol. 60, No. 9, pp. 2936-42, Sept. 2013,

40. Bandgap engineering of group IV materials for complementary n and p tunneling field effect transistors, Kotlyar, R.; Avci, U.E.; Cea, S.; Rios, R.; Linton, T.D.; Kuhn, K.J.; Young, I.A., Applied Physics Letters, v 102, n 11, March 18, 2013.

39. Effects of alternating current voltage amplitude and oxide capacitance on mid-gap interface state defect density extractions in InGaAs capacitors, Monaghan, Scott ; O'Connor, Eamon ; Povey, Ian M. ; Sheehan, Brendan J. ; Cherkaoui, Karim ; Hutchinson, Barry J. A. ; Hurley, Paul K. ; Ferdousi, Fahmida ; Rios, Rafael ; Kuhn, Dr. Kuhn J. ; Rahman, Anisur, Journal of Vacuum Science & Technology B: Microelectronics and Nanometer Structures, Vol: 31 , No: 1, 2013, pp: 01A119 - 01A119-8.

38. Considerations for Ultimate CMOS Scaling, Dr. Kuhn J. Kuhn, invited review paper, IEEE Trans. on Elec. Dev., Vol: 59 , No: 7, 2012 , pp. 1813 – 1828 (won the Paul Rappaport Award)

37. Does the low hole transport mass in <110> and <111> Si nanowires lead to mobility enhancements at high field and stress: a self-consistent tight-binding study, R. Kotlyar, T. D. Linton, R. Rios, M. D. Giles, S. M. Cea, K. J. Kuhn, Michael Povolotskyi, Tillmann Kubis, and Gerhard Klimeck, Vol: 111 , No: 12, 2012, pp 123718 - 123718-11

36. Comparison of Junctionless and Conventional Trigate Transistors With Lg Down to 26 nm, Rios, R.; Cappellani, A.; Armstrong, M.; Budrevich, A.; Gomez, H.; Pai, R.; Rahhal-orabi, N.; Kuhn, K., IEEE Electron Device Letters, Vol. 32, No. 9, 2011, pp. 1170 - 1172

35. Process Technology Variation, Kuhn, K.J.; Giles, M.D.; Becher, D.; Kolar, P.; Kornfeld, A.; Kotlyar, R.; Ma, S.T.; Maheshwari, A.; Mudanai, S., IEEE Transactions on Electron Devices, Aug. 2011, vol.58, no.8, pp. 2197-208.

34. Moore's crystal ball: Device physics and technology past the 15nm generation, Kuhn, K.J., Microelectronic Engineering, July 2011, vol.88, no.7, pp. 1044-9.

33. Variability in nanoscale CMOS technology, Kuhn, K.J., K. Sci. China Inf. Sci. (2011) 54: 936. doi:10.1007/s11432-011-4219-6 (May 5, 2011).

32. Compressive Uniaxial Stress Bandstructure Engineering for Transferred-Hole Devices, Kotlyar, R.; Giles, M.D.; Mudanai, S.P.; Kuhn, K.J.; Cea, S.M.; Linton, T.D.; Pillarisetty, R.; IEEE Elec. Dev. Lett. Vol. 31, No. 8, 2010, pp. 878-880.

31. Managing process variation in Intel's 45 nm CMOS technology, Kuhn, K., Kenyon, C., Kornfeld, A., et al. Intel Technology Journal Volume: 12 Issue: 2 Pages: 93-4 Published: 17 June 2008

30. Analytical Modeling of Output Conductance in Long-Channel Halo-Doped MOSFETs, Electron Devices, Mudanai, S.; Shih, W.-K.; Rios, R.; Xi, X.; Rhew, J.-H.; Kuhn, K.; Packan, P.;, IEEE Transactions on Volume 53, Issue 9, Sept. 2006 Page(s):2091 - 2097

29. A 90-nm logic technology featuring strained-silicon, Thompson, S.E.; Armstrong, M.; Auth, C.; Alavi, M.; Buehler, M.; Chau, R.; Cea, S.; Ghani, T.; Glass, G.; Hoffman, T.; Jan, C.-H.; Kenyon, C.; Klaus, J.; Kuhn, K.; Zhiyong Ma; Mcintyre, B.; Mistry, K.; Murthy, A.; Obradovic, B.; Nagisetty, R.; Phi Nguyen; Sivakumar, S.; Shaheed, R.; Shifren, L.; Tufts, B.; Tyagi, S.; Bohr, M.; El-Mansy, Y., IEEE Transactions on Electron Devices, vol.51, no.11, Nov. 2004. p. 1790-7.

28. Integration of mixed-signal elements into a high-performance digital CMOS process. Kuhn, K.J.; Ahmed, S.; Vandervoom, P.; Murthy, A. Intel Technology Journal, no.2, 2002

27. Elevated temperature performance of pseudomorphic AlGaAs/InGaAs MODFETs. Zurek, S.J.; Darling, R.B.; Kuhn, K.J.; Foisy, M.C. IEEE Transactions on Electron Devices, vol.45, no.1, Jan. 1998. p. 2-8

26. Synthetic wide bandpass X-ray polarizers. Cross, J.O.; Bennett, B.R.; Bell, M.I.; Kuhn, K.J. Applied Physics Letters, vol.70, no.17, 28 April 1997. p. 2224-6

25. Electro-optic polymer light modulator based on surface plasmon resonance. Jung, C.; Yee, S.; Kuhn, K. Applied Optics, vol.34, no.6, 20 Feb. 1995. p. 946-9

24. A "hands-on" course in consumer electronics design. Hannaford, B.; Kuhn, K. Mechatronics, vol.5, no.7, Oct. 1995. p. 753-62 Journal Paper

23. Finite element solutions to GaAs-AlAs quantum wells with connection matrices at heterojunctions. Li, T.L.; Kuhn, K.J. Journal of Computational Physics, vol.115, no.2, Dec. 1994. p. 288-95

22. Integrated optics waveguide modulator based on surface plasmon resonance. Jung, C.; Yee, S.; Kuhn, K. Journal of Lightwave Technology, vol.12, no.10, Oct. 1994. p. 1802-6

21. Effects of spin-orbit interaction on the envelope-function equations for semiconductor heterostructures. Li, T.L.; Kuhn, K.J. Physical Review B (Condensed Matter), vol.50, no.12, 15 Sept. 1994. p. 8589-601

20. Effects of mass discontinuity on the numerical solutions to quantum wells using the effective mass equation. Li, T.L.; Kuhn, K.J. Journal of Computational Physics, vol.110, no.2, Feb. 1994. p. 292-300

19. Validity of the connection-matrix approach to GaAs-Al/sub x/Ga/sub 1-x/As quantum wells. Li, T.L.; Kuhn, K.J. Physical Review B (Condensed Matter), vol.49, no.4, 15 Jan. 1994. p. 2608-14

18. Optical properties due to intersubband transitions in n-type quantum wells including the effects of the exchange interaction. Sengers, A.J.; Tsang, L.; Kuhn, K.J. Physical Review B (Condensed Matter), vol.48, no.20, 15 Nov. 1993. p. 15116-22

17. Band-offset ratio dependence on the effective-mass Hamiltonian based on a modified profile of the GaAs-Al/sub x/Ga/sub 1-x/As quantum well. Li, T.L.; Kuhn, K.J. Physical Review B (Condensed Matter), vol.47, no.19, 15 May 1993. p. 12760-70

16. Use of active loads with MSM photodetectors in digital GaAs MESFET photoreceivers. Darling, R.B.; Youn, H.J.; Kuhn, K.J. Journal of Lightwave Technology, vol.10, no.11, Nov. 1992. p. 1597-605

15. Mobility of strained and dislocated In/sub x/Ga/sub 1-x/As semiconductor material. Kuhn, K.J.; Darling, R.B. IEEE Transactions on Electron Devices, vol.39, no.6, June 1992. p. 1288-94

14. Dislocation scattering in n-type modulation doped Al/sub 0.3/Ga/sub 0.7/As/In/sub x/Ga/sub 1-x/As/Al/sub 0.3/Ga/sub 0.7/As quantum wells. Zhao, D.; Kuhn, K.J. IEEE Transactions on Electron Devices, vol.38, no.12, Dec. 1991. p. 2582-9

13. Free carrier induced changes in the absorption and refractive index for intersubband optical transitions in Al/sub x/Ga/sub 1-x/As/GaAs/Al/sub x/Ga/sub 1-x/As quantum wells. Kuhn, K.J.; Iyengar, G.U.; Yee, S. Journal of Applied Physics, vol.70, no.9, 1 Nov. 1991. p. 5010-17

12. Electric field effects in AlGaAs-GaAs symmetric and asymmetric coupled quantum wells. Juang, C.; Kuhn, K.J.; Darling, R.B. IEEE Journal of Quantum Electronics, vol.27, no.9, Sept. 1991. p. 2122-8

11. Effect of etch treatment prior to Schottky contact fabrication on In/sub 0.05/Ga/sub 0.95/As. Johnson, M.J.; Kuhn, K.J.; Darling, R.B. Applied Physics Letters, vol.58, no.17, 29 April 1991. p. 1893-5

10. An enhanced and linear Stark shift in n-i-n AlGaAs/GaAs symmetric and asymmetric coupled quantum wells. Kuhn, K.J.; Cheng Juang; Darling, R.B. Journal of Applied Physics, vol.69, no.5, 1 March 1991. p. 3135-41

9. AlGaAs-GaAs multiple-quantum-well spectrally tunable photoconductors. Youn, H.J.; Darling, R.B.; Kuhn, K.J. IEEE Photonics Technology Letters, vol.3, no.2, Feb. 1991. p. 159-61

8. Effect of AlGaAs window and buffer layers on the response characteristics of GaAs photoconductive detectors. Youn, H.J.; Darling, R.B.; Kuhn, K.J. Applied Physics Letters, vol.57, no.19, 5 Nov. 1990. p. 2001-3

7. Selective etching of GaAs and Al/sub 0.30/Ga/sub 0.70/As with citric acid/hydrogen peroxide solutions. Juang, C.; Kuhn, K.J.; Darling, R.B. Journal of Vacuum Science & Technology B (Microelectronics Processing and Phenomena), vol.8, no.5, Sept.-Oct. 1990. p. 1122-4

6. Stark shift and field-induced tunneling in Al/sub x/Ga/sub 1-x/As/GaAs quantum-well structures. Juang, C.; Kuhn, K.J.; Darling, R.B. Physical Review B (Condensed Matter), vol.41, no.17, 15 June 1990. p. 12047-53

5. An indium-free substrate holder for radiative heating of quarter-wafer molecular-beam epitaxy samples. Kuhn, K.J. Review of Scientific Instruments, vol.61, no.1, pt.1, Jan. 1990. p. 184-5

4. Variation in GaAs surface oxide desorption temperature as a function of shuttered aluminum oven temperature. Kuhn, K.J.; Pubanz, G.A. Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films), vol.7, no.6, Nov.-Dec. 1989. p. 3265-8

3. Static gas conduction cooled slab geometry Nd:glass laser. Reed, M.; Kuhn, K.; Unternahrer, J.; Byer, R.L. IEEE Journal of Quantum Electronics, vol.QE-21, no.5, May 1985. p. 412-14

2. The slab geometry laser. I. Theory. Eggleston, J.M.; Kane, T.J.; Kuhn, K.; Unternahrer, J. IEEE Journal of Quantum Electronics, vol.QE-20, no.3, March 1984. p. 289-301

1. Implementation of Distributed Microprocessor Systems in Custom Heavy Trucks, K.J. Kuhn, 1979-80 IEEE Student Papers, Vol. TT0114 IEEE, pg. 334-342.

CONFERENCE PUBLICATIONS

54. Bias temperature instability variation on SiON/Poly, HK/MG and trigate architectures, C. Prasad, M. Agostinelli, J. Hicks, S. Ramey, C. Auth, K. Mistry, S. Natarajan, P. Packan, I. Post, S. Bodapati, M. Giles, S. Gupta, S. Mudani and K. Kuhn, 2014 IEEE International Reliability Physics Symposium (IRPS), June 2014.

53. Semiconductors Stand Aside, the Age of Metals is Here! K. Kuhn, A. Sanchez, C. George, R. Rios, J. Clarke, J. Greer, Lester Eastman Conference, Cornell, May 2014.

52. The ultimate CMOS device and beyond, Kuhn, K.J. ; Avci, U. ; Cappellani, A. ; Giles, M.D. ; Haverty, M. ; Seiyon Kim ; Kotlyar, R. ; Manipatruni, S. ; Nikonov, D. ; Pawashe, C. ; Radosavljevic, M. ; Rios, R. ; Shankar, S. ; Vedula, R. ; Chau, R. ; Young, I. 2012 IEEE International Electron Devices Meeting (IEDM), pp. 171-174.

51. Understanding the feasibility of scaled III–V TFET for logic by bridging atomistic simulations and experimental results, Avci, U.E. ; Hasan, S. ; Nikonov, D.E. ; Rios, R. ; Kuhn, K. ; Young, I.A., Symposium on VLSI Technology (VLSIT), 2012, pp: 183 – 184.

50. Beyond the Planar Transistor: Progress in Next Generation Switches, K. Kuhn, Int'l Symposium on Adv. Gate. Stack Technology, Oct. 19-21, 2011 New York

49. Moore's Crystal Ball: Device Physics and Technology Past the 15nm Generation, K. Kuhn, INFOS 2011 (June 22, 2011, France)

48. Comparison of power and performance for the TFET and MOSFET and considerations for P-TFET, Avci, U.E.; Rios, R.; Kuhn, K.J.; Young, I.A., IEEE Conference on Nanotechnology (IEEE-NANO), 2011 11th, pp. 869 – 872

47. Comparison of performance, switching energy and process variations for the TFET and MOSFET in logic, Avci, U.E.; Rios, R.; Kuhn, K.; Young, I.A., 2011 Symposium on VLSI Technology (VLSIT), 2011 , pp. 124 – 125

46. CMOS scaling for the 22nm node and beyond: Device physics and technology, Kuhn, K.J., 2011 International Symposium on VLSI Technology, Systems and Applications (VLSI-TSA), 2011 , pp. 1 – 2

45. Past, Present and Future: SiGe and CMOS Transistor Scaling. K. J. Kuhn, A. Murthy, R. Kotlyar, and M. Kuhn, ECS 2010, Oct. 10, Las Vegas, CA, USA.

44. Peering into Moore's Crystal Ball, Transistor Scaling beyond the 15nm node, K. J. Kuhn, Int'l Symposium on Adv. Gate. Stack Technology, Sept. 29th, 2010; Albany, NY, USA.

43. CMOS transistor scaling past 32nm and implications on variation, K. Kuhn, 2010 IEEE/SEMI Advanced Semiconductor Manufacturing Conference (ASMC), ASMC'2010, 11-13 July 2010, San Francisco, CA, USA, pp. 241-246.

42. Next Steps in Moore's Law: Transistor Scaling for the 15nm node and beyond, K. Kuhn, Nikkei Electronics Symposium, June 29th, 2010.

41. Technology options for 22nm and beyond, K. Kuhn, Technology, Kuhn, K.J.; Liu, M.Y.; Kennel, H.; 2010 International Workshop on Junction Technology (IWJT), IWJT'10, 10-11 May 2010, Shanghai, China, pp. 1-6.

40. CMOS technology beyond 22nm, K. Kuhn, 12th IEEE International Workshop on Cellular Nanoscale Neetworks and Applications, CNNA 2010, February 3-5 Berkeley, California

39. Transistor architecture: 45nm and beyond, K. Kuhn, Intel European Research and Innovation Conference, 8-10th September 2009, Leixlip, Co. Kildare.

38. Moore's Law Past 32nm: The Challenges in Physics and Technology Scaling, K. Kuhn, Solid State Devices and Materials Conference (SSDM), September 18, 2009, Sendai, Japan.

37. CMOS scaling beyond 32 nm: challenges and opportunities, Kuhn, K.J., 2009 46th ACM/IEEE Design Automation Conference (DAC), 26-31 July 2009, San Francisco, CA, USA, Pages: 310-13 Published: 2009

36. Future device scaling: beyond traditional CMOS, Tyagi, S., Auth, C., Ban, I., et al., 2009 2nd International Workshop on Electron Devices and Semiconductor Technology (IEDST), 1-2 June 2009, Mumbai, India, (IEDST) Pages: 4 pp. Published: 2009

35. Variation in 45nm and Implications for 32nm and Beyond, K. Kuhn, NMI International Conference on CMOS Variability, 12th & 13th May 2009, London, UK.

34. Moore's law past 32 nm: future challenges in device scaling, Kuhn, K.J., 2009 13th International Workshop on Computational Electronics (IWCE 2009), 27-29 May 2009, Beijing, China, (IWCE 2009) Pages: 6 pp. Published: 2009

33. 22 nm Device Architecture and Performance Elements, K.J. Kuhn, IEEE International Electron Devices Meeting, 15-17 December 2008, San Francisco, CA, USA , IEDM short course.

32. High performance hi-k + metal gate strain enhanced transistors on (110) silicon, Packan, P., Cea, S., Deshpande, H., Kuhn, K, et. al. IEDM 2008. IEEE International Electron Devices Meeting, 15-17 December 2008, San Francisco, CA, USA, IEDM 2008. IEEE International Electron Devices Meeting. Technical Digest Pages: 4 pp. Published: 2008

31. 45 nm high-k + metal gate strain-enhanced transistors, Auth, C., Cappellani, A., Chun, J.-S., Kuhn, K. et al, 2008 Symposium on VLSI Technology, 17-20 June 2008, Honolulu, HI, USA, Pages: 128-9 Published: 17 June 2008

30. Dielectric breakdown in a 45 nm high-K/metal gate process technology, Prasad, C., Agostinelli, M., Auth, C., Kuhn, K. et al, 2008 IEEE International Reliability Physics Symposium (IRPS), 27 April-1 May 2008, Phoenix, AZ, USA, Pages: 667-8 Published: 2008

29. BTI reliability of 45 nm high-K + metal-gate process technology, Pae, S., Agostinelli, M., Brazier, M., Kuhn, K, et al. 2008 IEEE International Reliability Physics Symposium (IRPS), 27 April-1 May 2008, Phoenix, AZ, USA, (IRPS) Pages: 352-7 Published: 2008

28. Reducing variation in advanced logic technologies: approaches to process and design for manufacturability of nanoscale CMOS, Kuhn, K.J., 2007 IEEE International Electron Devices Meeting - IEDM '07, 10-12 December 2007, Washington, DC, USA, IEDM '07 Pages: 471-4 Published: 2007

27. A 45 nm logic technology with high-k+metal gate transistors, strained silicon, 9 Cu interconnect layers, 193 nm dry patterning, and 100% Pb-free packaging, Mistry, K., Allen, C., Auth, C., Kuhn, K. et al., 2007 IEEE International Electron Devices Meeting - IEDM '07, 10-12 December 2007, Washington, DC, USA , IEDM '07 Pages: 247-50 Published: 2007

26. High performance 35nm L/sub GATE/ CMOS transistors featuring NiSi metal gate (FUSI), uniaxial strained silicon channels and 1.2nm gate oxide, Ranade, P.; Ghani, T.; Kuhn, K.; Mistry, K.; Pae, S.; Shifren, L.; Stettler, M.; Tone, K.; Tyagi, S.; Bohr, M.; Electron Devices Meeting, 2005. IEDM Technical Digest. IEEE International, 5-7 Dec. 2005 Page(s):4 pp.

25. Noise performance of 90 nm CMOS technology, Becher, D.; Banerjee, G.; Basco, R.; Hung, C.; Kuhn, K.; Wei-Kai Shih, 2004 IEEE MTT-S International Microwave Symposium Digest (IEEE Cat. No.04CH37535). Piscataway, NJ, USA: IEEE, 2004. p. 17-20 Vol.1. Conference Paper.

24. A comparison of state-of-the-art NMOS and SiGe HBT devices for analog/mixed-signal/RF circuit applications, Kuhn, K.; Basco, R.; Becher, D.; Hattendorf, M.; Packan, P.; Post, I.; Vandervoorn, P.; Young, I., 2004 Symposium on VLSI Technology. Digest of Technical Papers (IEEE Cat. No.04CH37526). Gaithersburg, MD, USA: Widerkehr and Associates, 2004. p. 224-5. Conference Paper.

23. A 90 nm communication technology featuring SiGe HBT transistors, RF CMOS, precision R-L-C RF elements and 1 /spl mu/m/sup 2/ 6-T SRAM cell, Kuhn, K.; Agostinelli, M.; Ahmed, S.; Chambers, S.; Cea, S.; Christensen, S.; Fischer, P.; Gong, J.; Kardas, C.; Letson, T.; Henning, L.; Murthy, A.; Muthali, H.; Obradovic, B.; Packan, P.; Pae, S.W.; Post, I.; Putna, S.; Raol, K.; Roskowski, A.; Soman, R, "" Electron Devices Meeting, 2002. IEDM '02. Digest. International , 8-11 Dec. 2002 Page(s): 73 -76

22. A 90 nm Generation BiCMOS Technology for Analog, Mixed-signal, and RF Applications, K. Kuhn, S. Chambers, C. Kardas, T. Letson, A-.Murthy and P. Packan, Intel Process Technology Conference, October, 17, 2002. (Best of session paper award)

21. Scaling challenges for 0.13 mu m generation shallow trench isolation, Kuhn, K.J.; Din-how Mei; Post, I.; Neirynck, J., 2001 IEEE International Symposium on Semiconductor Manufacturing. ISSM 2001. Conference Proceedings (Cat. No.01CH37203). Piscataway, NJ, USA: IEEE, 2001. p. 187-90 Conference Paper

20. Scaling challenges for 0.13 mu m generation shallow trench isolation, Kuhn, K.J.; Din-how Mei; Post, I.; Neirynck, J., and Au, W., Intel Process Technology Conference, October, 10, 2000.

19. Electrical critical dimension metrology for 100 nm linewidths and below. Grenville, A.; Coombs, B.; Hutchinson, J.; Kuhn, K. Proceedings of the SPIE - The International Society for Optical Engineering, vol.4000, pt.1-2, 2000. p. 452-9 Conference Paper

18. The performance of a wide band X-ray Bragg polarizer grown by molecular beam epitaxy, Cross, J.O.; Bennett, B.R.; Bell, M.I.; Kuhn, K.J., , AIP Conference Proceedings, no.417, 1997. p. 117

17. Solving the 3 and 4 state laser systems, Dr. Kuhn Kuhn, regular paper, Fifth annual conference on the teaching of mathematics, Baltimore, Maryland, June 21, 1996.

16. An integrated course in laser engineering, K. Kuhn, regular paper #1232, ASEE 1996 annual conference, Washington DC, June 22-26, 1996.

15. Development of a course in Consumer Electronics, K. Kuhn and B. Hannaford, regular paper #3232, ASEE 1996 annual conference, Washington DC, June 22-26, 1996.

14. An Erbium-doped fiber laser, C. Cornish and K. Kuhn, 1995 Progress in Electromagnetics Research Symposium, July 24-28, 1995.

13. Development of a course in Consumer Electronics, K. Kuhn and B. Hannaford, Session 3B, Mechatronics Conference, Stanford, July 15-17, 1994.

12. Integrated optical waveguide modulator using long range surface plasmon resonance, C. Jung, S. Yee and K. Kuhn, OSA Integrated Photonics Research Conference, San Francisco, CA. February 17-19 (1994)

11. Evaluation of an ion-exchanged integrated optic waveguide for solution phase chemical sensing. Kuhn, K.J.; Burgess, L.W. Proceedings of the SPIE - The International Society for Optical Engineering, vol.1796, 1993. p. 332-42 Conference Paper

10. A. Sengers, G. Iyengar, L. Tsang and K. Kuhn, "Optical Properties due to Intersubband Transitions in n-type Quantum Wells Including the Effects of the Exchange Interaction", 1993 March meeting of the American Physical Society, Seattle, WA 22-26 March 1993.

9. Free carrier induced changes in the absorption and refractive index for intersubband optical transitions in Al/sub x/Ga/sub 1-x/As/GaAs/Al/sub x/Ga/sub 1-x/As quantum wells. Iyengar, G.U.; Kuhn, K.J.; Yee, S. In: Gallium Arsenide and Related Compounds 1991. Proceedings of the Eighteenth International Symposium. Bristol, UK: IOP, 1992. p. 431-6 Conference Paper

8. Free carrier induced changes in the absorption and refractive index for intersubband optical transitions in $Al_xGa_{1-x}As/GaAs/Al_xGa_{1-x}As$ quantum wells, G. Iyengar, K. Kuhn, and S. Yee, Conference Proceedings, 17th International Symposium on GaAs and Related Compounds, September 9-12, 1991; Seattle, WA.

7. Applications of Molecular Beam Epitaxy to Integrable Optical Devices, K.J. Kuhn, Professional program, Northcon/88, October 5, 1988.

6. Laser annealing of AlGaAs, E. Riemer, K. Song, K. Kuhn and T. Stoebe, Atomic and Molecular Processing of Electronics and Ceramic Materials, 23 Conf. on Ceramic Science, UW, August 30 to September 3, 1987.

5. Amplified Spontaneous Emission in Slab Lasers, D.C. Brown, K.J. Kuhn, Kotik K. Lee and R.L. Byer, paper WE-5, Conference on Lasers and Electro-optics (CLEO), Anaheim, CA, June 1984.

4. Progress in high peak and average power lasers for soft X-ray production. Byer, R.L.; Kuhn, K.; Reed, M.; Trail, J. Proceedings of the SPIE - The International Society for Optical Engineering, vol.448, 1984. p. 2-7 Conference Paper

3. Conductive-cooling of Slab Lasers, K.J. Kuhn, T.J. Kane, and R.L. Byer, paper WE-3, 1982 Annual meeting of the Optical Society of America, Tucson, Arizona, October 1982.

2. Progress in slab geometry solid state lasers. Eggleston, J.M.; Kane, T.; Kuhn, K.; Byer, R.L. Proceedings of the SPIE - The International Society for Optical Engineering, vol.335, 1982. p. 104-8 Conference Paper

1. Implementation of distributed microprocessor systems in custom heavy trucks. Kuhn, K.J. In: Wescon/80 Conference Record. El Segundo, CA, USA: Electron. Conventions, 1980. p. SS2-3/1-8 Conference Paper

INVITED TECHNICAL PRESENTATIONS/SEMINARS :

Invited panel, IEDM, Variation and the End of the World, December, 2013.

Keynote, The End of Scaling?, ICTC, December 2013.

Invited seminar, CMOS and Beyond, Portland State University, October, 2013.

Keynote panel, CMOS and Beyond: Future Device Technology, ENF 2013, Ireland, June 2013.

Invited seminar, CMOS and Beyond: Future Device Technology for the Mobile World, IDF, May 2013.

Invited Workshop, The Future is Already Here: Evolving Concepts in Device and Materials Technology, AMAT, March 2013.

Invited paper, “The Ultimate CMOS Device and Beyond,” IEDM 2012, San Francisco.

Invited talk, Beyond Simply Small: Progress in Advanced Transistor Architectures, Cornell, November 2012.

Invited seminar, Demystifying Moore's Law How it Really Works!, IDF, Sept. 2012, San Francisco.

Invited talk, The Ultimate CMOS Device and Beyond, Ireland, April 2012.

Keynote: "MOS scaling for the 22nm node and beyond: Device physics and technology," April 24, 2011, Taiwan, VLSI-TSA

Plenary: "Moore's Crystal Ball: Device Physics and Technology Past the 15nm Generation," INFOS 2011 (June 22, 2011, France)

Keynote: "Beyond the Planar Transistor: Progress in Next Generation Switches," Int'l Symposium on Adv. Gate. Stack Technology, Oct. 19-21, 2011 New York

Invited seminar - "Polishing Moore's Crystal Ball: Advanced Transistor Architectures …and Beyond," K. Kuhn, March 30th. 2011, MIT, MTL seminar series.

Invited seminar - "Emerging Devices: Moore's Law and Advanced Transistor Architectures," K. Kuhn, Varian Technology Symposium, March 31st. 2011.

Keynote: "Scaling Electronics:Trends and Bottlenecks," K. Kuhn, April 4th. 2011, MIT Microphotonics meeting.

Invited seminar - "Gazing into Moore's Crystal Ball: Transistor Scaling after the 15nm node," K. Kuhn, Feb. 17th, 2010, Berkeley.

IEDM 2010 Short Course chair for 15nm technology, December 2010.

Plenary: Past, Present and Future: SiGe and CMOS Transistor Scaling, ECS 2010, Oct. 10, Las Vegas, CA, USA.

Keynote: Peering into Moore's Crystal Ball, Transistor Scaling beyond the 15nm node, Int'l Symposium on Adv. Gate. Stack Technology, Sept. 29th, 2010; Albany, NY, USA.

Plenary: CMOS transistor scaling past 32nm and implications on variation, 2010 IEEE/SEMI Advanced Semiconductor Manufacturing Conference (ASMC), ASMC'2010,11-13 July 2010, San Francisco, CA, USA

Keynote: Technology options for 22nm and beyond, K. Kuhn, 2010 International Workshop on Junction Technology (IWJT), IWJT'10, 10-11 May 2010, Shanghai, China, pp. 1-6.

Invited seminar: Next Steps in Moore's Law: Transistor Scaling for the 15nm node and beyond, Nikkei Electronics Symposium / June 29th, 2010.

Plenary - CMOS technology beyond 22nm, K. Kuhn, 12th IEEE International Workshop on Cellular Nanoscale Neetworks and Applications, CNNA 2010, February 3-5 Berkeley, California

Keynote - Transistor architecture: 45nm and beyond, K. Kuhn, Intel European Research and Innovation Conference, 8-10th September 2009, Leixlip, Co. Kildare.

Plenary - Moore's Law Past 32nm: The Challenges in Physics and Technology Scaling, K. Kuhn, Solid State Devices and Materials Conference (SSDM), September 18, 2009, Sendai, Japan.

Invited talk - CMOS scaling beyond 32 nm: challenges and opportunities, Kuhn, K.J., 2009 46th ACM/IEEE Design Automation Conference (DAC), 26-31 July 2009, San Francisco, CA, USA, Pages: 310-13 Published: 2009

Keynote - Variation in 45nm and Implications for 32nm and Beyond, K. Kuhn, NMI International Conference on CMOS Variability, 12th & 13th May 2009, London, UK.

Invited talk - Moore's law past 32 nm: future challenges in device scaling, Kuhn, K.J., 2009 13th International Workshop on Computational Electronics (IWCE 2009), 27-29 May 2009, Beijing, China, (IWCE 2009) Pages: 6 pp. Published: 2009

Invited – International Electron Device meeting – short course.
http://download.intel.com/pressroom/pdf/kkuhn/Kuhn_22nm_Device.pdf

Invited seminar - "45nm High-k + Metal Gate Logic Technology," K. Kuhn, May 2008, MIT, MTL laboratory.

Invited talk - Reducing variation in advanced logic technologies: approaches to process and design for manufacturability of nanoscale CMOS, Kuhn, K.J., 2007 IEEE International Electron Devices Meeting - IEDM '07, 10-12 December 2007, Washington, DC, USA, IEDM '07 Pages: 471-4

Invited seminar - "CMOS Transistor Architecture Challenges and Opportunities," K. Kuhn, September 2005, MIT, MTL laboratory.

Keynote - "Nanotechnology Challenges and Opportunities," K. Kuhn, January 2005, MIT, MTL laboratory.

Invited seminar - "Transistor Scaling and its Impact on Analog/RF Device Performance", Dr. Kuhn Kuhn, March 2005, Stanford University, invited seminar.

Invited seminar - “Advanced transistor architecture approaches and their implications for device and circuit performance,” Dr. Kuhn Kuhn, Intel Fellow’s Forum, October 2004.

Invited seminar - “Moore’s Law meets Materials Science”, Dr. Kuhn Kuhn, September 2004, University of Washington.

Invited seminar - “Centrino, convergence of computing and communications,” November 2003, Dr. Kuhn Kuhn, Stanford University, invited seminar.

Invited seminar - “Challenges in the parallel development of the 90nm communications (121x) and microprocessor (1262) process technologies,” Dr. Kuhn Kuhn, Intel Fellow’s Forum, October 2003.

Invited seminar - “RF/analog integration with 90nm digital CMOS”, Dr. Kuhn Kuhn, MIT invited seminar, March 2003

Invited seminar - "Femtosecond pulse laser technology", Dr. Kuhn Kuhn, Oregon State University, March 10, 1997.

Invited talk- "Symbolic Solvers and their impact on engineering education", Dr. Kuhn Kuhn, Fifth annual conference on the teaching of mathematics, Baltimore, Maryland, June 21, 1996.